

30 V, P-channel Trench MOSFET 24 March 2015

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-1	А
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -1 A; T_j = 25 °C		-	430	510	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source	2	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa259

6. Ordering information

Table 3. Ordering information							
Type number							
	Name	Description	Version				
PMZ320UPE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMZ320UPE	ZW

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-1	А
		V_{GS} = -4.5 V; T_{amb} = 100 °C	[1]	-	-0.6	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-4	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	760	mW
		T _{sp} = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-0.7	А

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

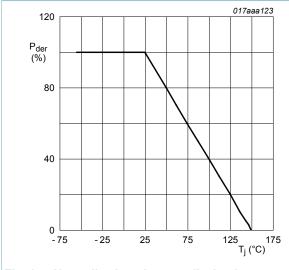
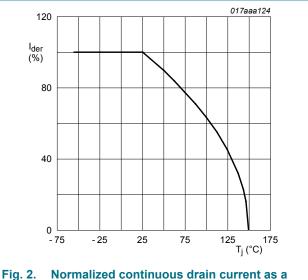
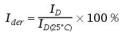


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

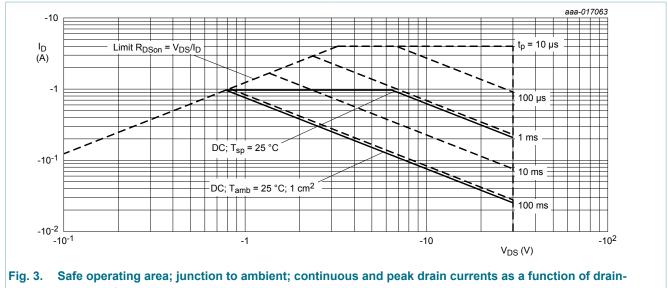


function of junction temperature



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source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

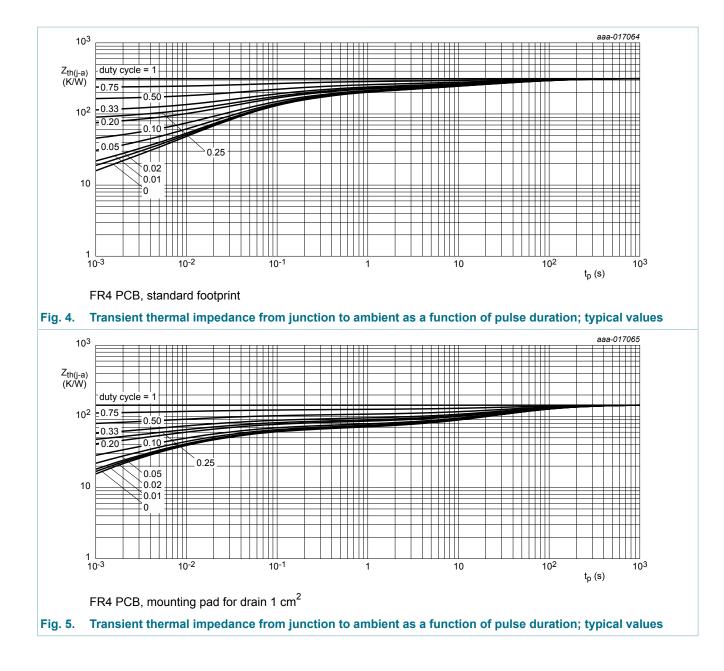
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
fr	thermal resistance	rom junction to	[1]	-	315	360	K/W
	from junction to ambient		[2]	-	145	165	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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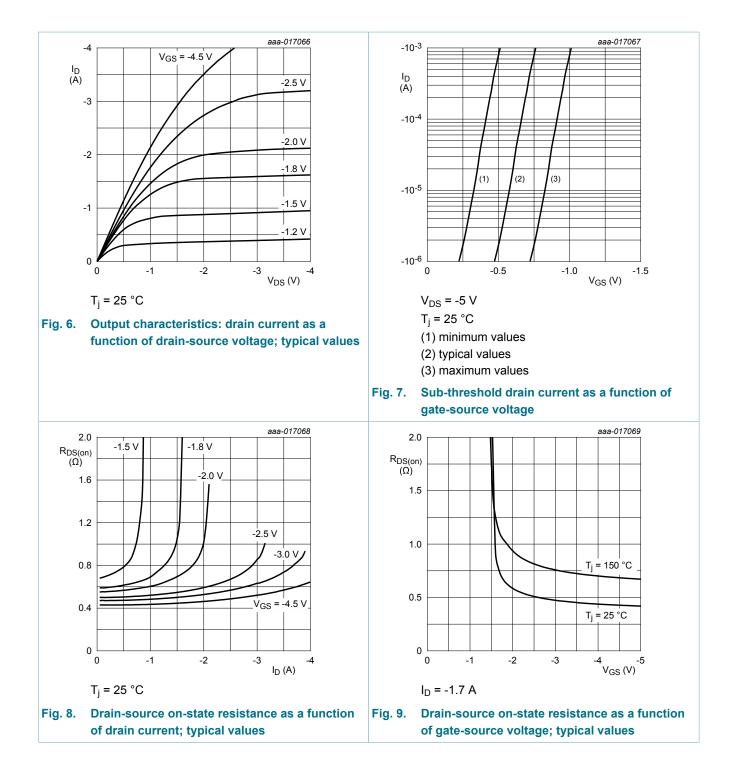


10. Characteristics

teristics drain-source breakdown voltage gate-source threshold voltage drain leakage current	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-30	-	-	V
breakdown voltage gate-source threshold voltage			-	-	V
voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45			
drain leakage current		-0.40	-0.7	-0.95	V
	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
	V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
	V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
	V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
	V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
	V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
drain-source on-state	V _{GS} = -4.5 V; I _D = -1 A; T _j = 25 °C	-	430	510	mΩ
resistance	V _{GS} = -4.5 V; I _D = -1 A; T _j = 150 °C	-	680	810	mΩ
	V _{GS} = -2.5 V; I _D = -0.8 A; T _j = 25 °C	-	570	770	mΩ
	V _{GS} = -1.8 V; I _D = -0.25 A; T _j = 25 °C	-	750	1140	mΩ
	V _{GS} = -1.5 V; I _D = -0.01 A; T _j = 25 °C	-	950	1610	mΩ
forward transconductance	V _{DS} = -10 V; I _D = -1 A; T _j = 25 °C	-	2.1	-	S
racteristics	1	I			
total gate charge	V_{DS} = -15 V; I _D = -1 A; V _{GS} = -4.5 V;	-	1.4	-	nC
gate-source charge	T _j = 25 °C	-	0.2	-	nC
gate-drain charge		-	0.3	-	nC
input capacitance	V_{DS} = -15 V; f = 1 MHz; V_{GS} = 0 V;	-	122	-	pF
output capacitance	T _j = 25 °C	-	11	-	pF
reverse transfer capacitance		-	9	-	pF
turn-on delay time	V_{DS} = -15 V; I _D = -1 A; V _{GS} = -4.5 V;	-	3	-	ns
rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	6	-	ns
turn-off delay time		-	22	-	ns
fall time		-	5	-	ns
diode	· · · · · · · · · · · · · · · · · · ·	I			
	resistanceforward transconductanceracteristicstotal gate chargegate-source chargegate-drain chargeinput capacitanceoutput capacitanceoutput capacitanceturn-on delay timerise timeturn-off delay time	$\begin{tabular}{ c c c c } \hline V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = 2.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -2.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -2.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -4.5 \ V; \ I_D = -1 \ A; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -4.5 \ V; \ I_D = -1 \ A; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -2.5 \ V; \ I_D = -0.25 \ A; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -1.5 \ V; \ I_D = -0.25 \ A; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -1.5 \ V; \ I_D = -0.01 \ A; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -1.5 \ V; \ I_D = -0.01 \ A; \ T_j = 25 \ ^{\circ}C \\ \hline V_{GS} = -1.5 \ V; \ I_D = -1 \ A; \ V_{GS} = -4.5 \ V; \\ \hline gate-source \ charge \\ \hline gate-drain \ charge \\ \hline input \ capacitance \\ \hline V_{DS} = -15 \ V; \ I_D = -1 \ A; \ V_{GS} = -4.5 \ V; \\ \hline gate-drain \ charge \\ \hline input \ capacitance \\ \hline V_{DS} = -15 \ V; \ f = 1 \ MHz; \ V_{GS} = 0 \ V; \\ \hline turn-on \ delay \ time \\ \hline v_{DS} = -15 \ V; \ I_D = -1 \ A; \ V_{GS} = -4.5 \ V; \\ \hline rise \ time \\ \hline turn-on \ delay \ time \\ \hline fall \ time \\ \hline diode \\ \hline \hline diode \\ \hline \end{tabular}$	$\begin{tabular}{ c c c c } \hline V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}C & $-$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	$\begin{tabular}{ c c c c } \hline V_{GS} = -4.5 V; V_{DS} = 0 V; T_{j} = 25 °C & $$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	$\begin{tabular}{ c c c c } \hline V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}C & - & - & 100 \\ \hline V_{GS} = 2.5 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}C & - & - & 100 \\ \hline V_{GS} = -2.5 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}C & - & 430 \ 510 \\ \hline V_{GS} = -2.5 \ V; \ V_{D} = -1 \ A; \ T_{j} = 25 \ ^{\circ}C & - & 430 \ 510 \\ \hline V_{GS} = -4.5 \ V; \ I_{D} = -1 \ A; \ T_{j} = 25 \ ^{\circ}C & - & 680 \ 810 \\ \hline V_{GS} = -2.5 \ V; \ I_{D} = -0.8 \ A; \ T_{j} = 25 \ ^{\circ}C & - & 570 \ 770 \ \hline V_{GS} = -1.8 \ V; \ I_{D} = -0.8 \ A; \ T_{j} = 25 \ ^{\circ}C & - & 570 \ 750 \ 1140 \\ \hline V_{GS} = -1.8 \ V; \ I_{D} = -0.01 \ A; \ T_{j} = 25 \ ^{\circ}C & - & 950 \ 1610 \ \hline forward \ transconductance \ V_{DS} = -10 \ V; \ I_{D} = -1 \ A; \ T_{j} = 25 \ ^{\circ}C & - & 0.2 \ - & 0.2 \ - & 0.2 \ - & 0.3 \ - &$

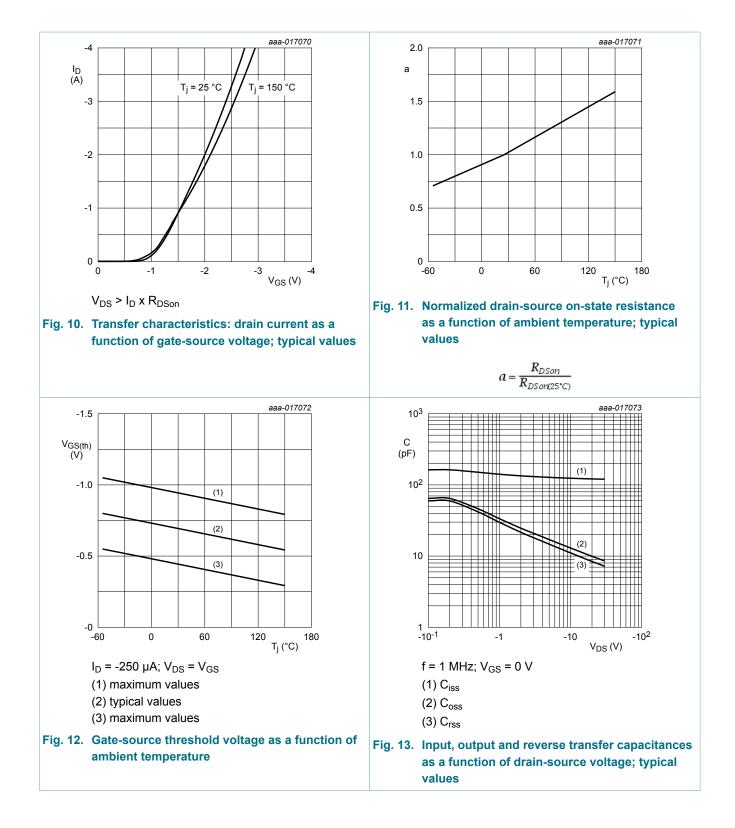
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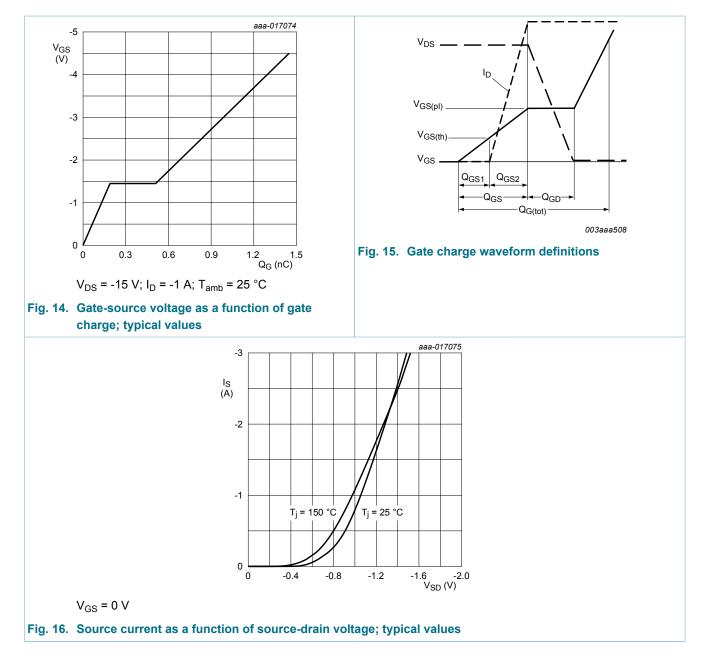
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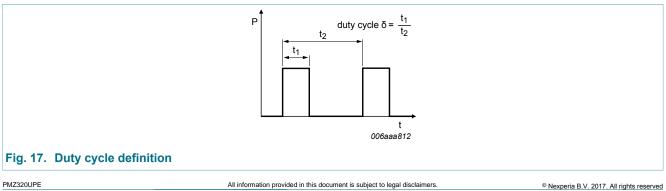
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11. Test information



12. Package outline

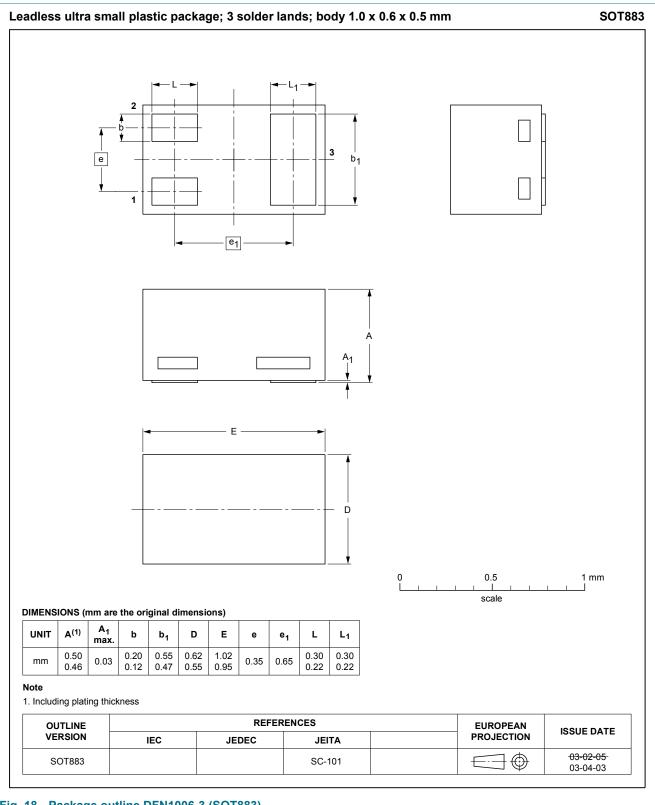
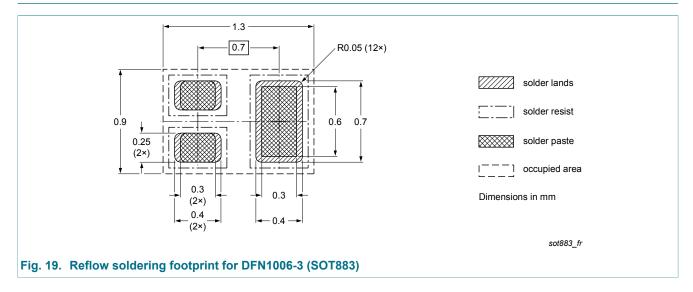


Fig. 18. Package outline DFN1006-3 (SOT883)
PMZ320UPE All information

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13. Soldering



14. Revision history

Table 8. Revision his	Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMZ320UPE v.1	20150324	Product data sheet	-	-		

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16. Contents

1	General description1
2	Features and benefits1
3	Applications1
4	Quick reference data 1
5	Pinning information2
6	Ordering information2
7	Marking2
8	Limiting values3
9	Thermal characteristics4
10	Characteristics6
11	Test information9
12	Package outline 10
13	Soldering11
14	Revision history12
15	Legal information13
15.1	Data sheet status 13
15.2	Definitions13
15.3	Disclaimers13
15.4	Trademarks 14

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